MMBD217SEW

SILICON EPITAXIAL PLANAR SWITCHING DIODE

Applications

Ultra high speed switching





SOT-323 Plastic Package Marking Code: **A7**

Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V _{RM}	80	V
Reverse Voltage	V _R	80	V
Average Rectified Forward Current (Single)	Ι _ο	100	mA
Maximum (Peak) Forward Current (Single)	I _{FM}	300	mA
Peak Forward Surge Current ($t_p = 1 \ \mu s$)	I _{FSM}	4	А
Power Dissipation	P _d	200	mW
Junction Temperature	TJ	150	°C
Storage Temperature Range	T _s	- 55 to + 150	°C

Characteristics at T_a = 25 °C

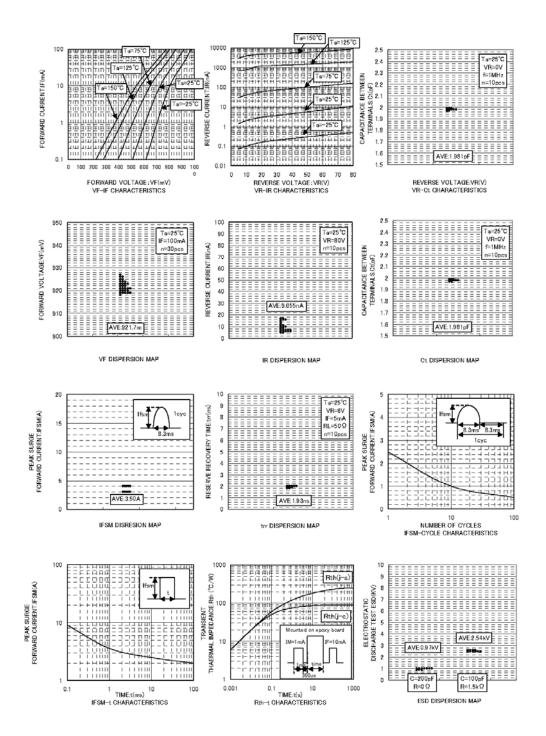
Parameter	Symbol	Max.	Unit
Forward Voltage at I _F = 100 mA	V _F	1.2	V
Reverse Current at V_R = 70 V	I _R	0.1	μΑ
Capacitance between Terminals at V_R = 6, f = 1 MHz	CT	3.5	pF
Reverse Recovery Time at I_F = 5 mA, V_R = 6 V, R_L = 50 Ω	t _{rr}	4	ns







Dated : 10/10/2008





SEMTECH ELECTRONICS LTD.

(Subsidiary of Sino-Tech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724)



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